Microwave Performance of an Optically Controlled AlGaAs/GaAs High Electron Mobility Transistor and GaAs MESFET

Raine N. Simons and Kul B. Bhasin

Lewis Research Center
Cleveland, Ohio

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MICROWAVE PERFORMANCE OF AN OPTICALLY CONTROLLED AlGaAs/GaAs HIGH ELECTRON MOBILITY TRANSISTOR AND GaAs MESFET

Rainee N. Simons* and Kul B. Bhasin

National Aeronautics and Space Administration
Lewis Research Center
Cleveland, Ohio 44135

Abstract

Direct current and also the microwave characteristics of optically illuminated AlGaAs/GaAs HEMT are experimentally measured for the first time and compared with that of GaAs MESFET. The results showed that the average change in the gain is 2.8 dB under 1.7 mW/cm² optical intensity at 0.83 μm. Further, the effect of illumination on S-parameters is more pronounced when the devices are biased close to pinch-off. Novel applications of optically illuminated HEMT as a variable gain amplifier, high-speed high-frequency photo detector, and mixer are demonstrated.

Introduction

Use of direct optical control of microwave semiconductor devices for optical injection locking, phase shifting, and signal distribution has the potential to enhance the performance of future space borne phased array antenna systems. Previous authors have experimentally investigated the effect of light on the dc as well as the microwave characteristics of IMPATT diodes and GaAs MESFETs. Their investigations show that these changes in the characteristics are due to photoconductivity and photovoltaic effects. Further, an analytical study, by the authors taking into consideration material properties of heterostructures showed that the heterostructures have a higher sensitivity to optical illumination. For this investigation was extended to microwave device structures, it was observed that the dc characteristics of an AlGaAs/GaAs High Electron Mobility Transistor (HEMT), when compared to that of a GaAs MESFET, are more sensitive to optical illumination than the semiconductor band gap.

In this paper, we present for the first time extensive experimental results which show the sensitivity to optical illumination, that is, the light induced voltage and as a consequence the changes in the drain to source current, the intrinsic transconductance, the scattering parameters, and the gain of an AlGaAs/GaAs HEMT. Further, from the de-embedded HEMT scattering parameters, the changes in the equivalent circuit element values due to optical illumination are also computed. In order to compare and contrast the performance of a HEMT with a MESFET, experiments are also carried out on two different GaAs MESFETs and these results are also presented here. Finally, three novel applications of optically illuminated HEMT as a variable gain amplifier, high-speed high-frequency photo detector, and mixer are demonstrated.

Experimental Setup

A low noise AlGaAs/GaAs High Electron Mobility Transistor (MPD-H503, Gould Inc.) with recessed Pi-gate of length 0.5 μm and width 280 μm, a low noise, low power GaAs MESFET (DYL 0503A, Gould Inc.) with recessed Pi-gate of length 0.3 μm and width 280 μm, and a medium power GaAs MESFET (RPX 2322, Raytheon Co.) with T-gate of length of 0.5 μm and width 500 μm are used for investigation. For optical illumination an AlGaAs/GaAs Laser diode (SL-620 S, Ortel Corp.) with a fiber pigtail, which operates at a wavelength of 0.83 μm and has a direct modulation bandwidth of 6 GHz is used. The optical power emitted from the 50 μm multimode graded index optical fiber pigtail as measured using a calibrated digital power meter and a photosensor (815, Newport Corp.) is 1.7 mW/cm². The tip of the fiber is held at a distance of 1 mm from the device.

These devices are mounted on a 0.375 by 0.375 in., 25 mil thick alumina carrier. The alumina carrier also accommodates a pair of 50 Ω coplanar waveguides (CPW) which serve as the signal input and also output ports. The device gate and drain pads and the source pad are wire bonded to the CPW center strip conductors and the ground plane respectively. The carrier is then mounted in a test fixture (Design Techniques, Inc.) which has two 3.5 mm coaxial connectors for external connection. The test fixture also has provision for ensuring repeatable pressure contact between the terminals of the CPWs on the carrier and the two 3.5 mm coaxial connectors on the fixture. A CPW calibration kit consisting of a 50 Ω through, two short circuits, and an open circuit on similar alumina carriers are used for calibrating the HP8510 automatic network analyzer and de-embedding

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*National Research Council - NASA Research Associate.
the device S-parameters. A block schematic of the entire experimental setup is shown in Fig. 1.

**dc Device Characteristics Under Illumination**

**Light Induced Voltage**

The light generated voltage $V_{lit}$ is obtained by plotting the measured gate current $I_g$ as a function of the reverse biased gate to source voltage $V_{gs}$, and extrapolating the graph till it intersects the X-axis. The intersection point is read as the light generated voltage, which from Fig. 2(a) and (b) for a AlGaAs/GaAs HEMT and a GaAs MESFET are 0.57 and 0.24 V respectively.

**Drain to Source Current, Transconductance, and Gain**

The measured drain to source current $I_{ds}$ as a function of the drain to source voltage $V_{ds}$ with and without optical illumination for an AlGaAs/GaAs HEMT and a GaAs MESFET are presented in Fig. 3(a) and (b) respectively. Figure 4 presents the measured dc transconductance $g_m$ for a GaAs MESFET. The $g_m$ is considered almost insensitive to optical illumination since the maximum change observed is less than 2 mhos.

The measured gain with and without optical illumination as a function of $V_{ds}$ for an AlGaAs/GaAs HEMT and a GaAs MESFET are presented in Fig. 5(a) and (b) respectively. As an example, for the case of a AlGaAs/GaAs HEMT, the gain increases by 2.5 dB at $V_{ds} = -0.95$ V and frequency equal to 26.5 GHz when the illumination is 1.7 mW/cm².

**Microwave Characteristics Under Illumination**

The S-parameters, namely $S_{11}$, $S_{22}$, and $S_{12}$ are measured as a function of the frequency and illumination (1.7 mW/cm²) with the devices biased close to saturation and also pinch-off. These bias points or operating points are labeled as points A and B respectively in Fig. 5(a) for the AlGaAs/GaAs HEMT and Fig. 5(b) for the GaAs MESFET.

The measured $S_{11}$ over the frequency range 0.045 to 26.5 GHz for AlGaAs/GaAs HEMT in pinch-off ($V_{gs} = -0.95$ V) condition is illustrated on a Smith Chart plot in Fig. 6(a). Similarly, $S_{22}$ is illustrated in Fig. 6(b). Figure 6(c) illustrates $S_{12}$ on a linear magnitude polar plot. In these figures L and D denotes that the measurements are carried out with or without illumination. A similar set of measurements have also been carried out for GaAs MESFET.

Thus from Fig. 6 it is observed that illumination does affect $S_{11}$, $S_{22}$, and $S_{12}$. Besides, this effect is more pronounced when the devices are biased close to pinch-off.

Using the CPW calibration kit and the through, short, delay (TSD) technique the influence of the small length of coplanar waveguide on either sides of the chip devices and the test fixture coaxial connectors are effectively removed. The small signal device equivalent circuit element values are next obtained from the de-embedded device S-parameters using the models in Refs. 9 and 10. As an example, Fig. 7 shows an increase in the gate and the source capacitances and a decrease in the gate to drain feedback capacitance, with optical illumination. In addition, the model also shows that the gate charging resistance $R_1$ and the channel resistance $R_0$ both decrease with optical illumination. The effect of these on the $f_t$, $f_{max}$, and noise figure are being further investigated.

**Optically Controlled HEMT as a Variable Gain Amplifier**

The feasibility of using an AlGaAs/GaAs HEMT as an optically controlled variable gain amplifier is clearly evident from the measured $S_{21}$ magnitude and phase characteristics shown in Figs. 8(a) to (d). Figure 8(a) and (b) when compared, show that the gain increases with illumination. Further it is interesting to observe that the phase of $S_{21}$ is insensitive to optical illumination as evident from Figs. 8(c) and (d).

**High Frequency HEMT Photodetector**

An experiment was conducted by illuminating the HEMT device with an optical signal which had been modulated with a 6 GHz RF signal and observing the output on a spectrum analyzer, which is shown in Fig. 9(a).

**HEMT Oscillator and HEMT Mixer with Optically Coupled LO**

The capacitance variation of HEMT with illumination is shown in Fig. 7. This can be successfully exploited in the design of an injection locked oscillator.

Preliminary experiments with a HEMT as a mixer show that it is possible to optically couple the local oscillator signal. This is achieved by directly modulating a laser diode at the local oscillator frequency (6 GHz). The laser diode output is then made to illuminate the gate region of the HEMT. The RF signal (9 GHz) is electrically coupled to the gate terminal. The resulting IF signal (3 GHz) as seen on a spectrum analyzer is shown in Fig. 9(b).

**Conclusions**

The paper presents for the first time extensive experimental results which show the sensitivity to optical illumination. The light induced voltage and as a consequence the changes in, the drain to source current, the intrinsic transconductance, the scattering parameters, and the gain of an AlGaAs/GaAs HEMT have been measured. The light induced voltage for a HEMT is observed to be 0.57 V and 0.24 V for MESFET at 0.83 µm wavelength. The higher $V_{lit}$ for HEMT is attributed to the higher increase in hole concentration $p$ mainly due to the absorption thickness $d$, (see Eq. 1). Further, from the de-embedded HEMT scattering
parameters the changes in the equivalent circuit
element values due to optical illumination are also
computed. These computations show an increase in
the gate and also the drain capacitances and a
decrease in the gate charging and also the channel
resistances. The effect of these changes on the
$f_T$, $f_{max}$ and the noise figure is being further
investigated. In addition to the above, experi-
mental results or GaAs MESFETs have also been pre-
sented for comparison.

In these experiments the HEMT is optically
illuminated by an AlGaAs/GaAs laser diode. This
feature further enhances the attractiveness of the
above experiments, since it leads to the possibil-
ity of integrating a HEMT and a laser diode on a
single MMIC chip to perform multiple circuit func-
tions optically, such as, switching, amplifier
gain control, phase shifting, and mixing. Such an
integration, when fully accomplished not only
promises improved MMIC circuit performance, but
also vastly simplifies the signal distribution and
beam steering in future phased array antenna.

Finally, three novel applications of an opti-
cally illuminated HEMT as a variable gain ampli-
fier, high frequency photo detector, and mixer are
demonstrated.

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FIGURE 1. - BLOCK SCHEMATIC OF THE EXPERIMENTAL SETUP.

FIGURE 2. - MEASURED $I_g$ VERSUS $V_{ds}$ FROM WHICH $V_{ds}$ IS OBTAINED. DISTANCE BETWEEN END OF FIBER AND DEVICE, 1 mm; $\lambda = 0.85 \mu m$; $P_{opt} = 1.5 \, \text{mW/cm}^2$. 

(A) DEVICE AlGaAs/GaAs HET (MODEL NO. MPD-H503); $V_{ds} = 0 \, \text{V}$. 

(B) DEVICE GaAs MESFET (MODEL NO. RFX 2322); $V_{ds} = 0 \, \text{V}$. 

FIGURE 3. - Measured $I_{ds}$ versus $V_{gs}$ with and without optical illumination.

FIGURE 4. - Measured $g_m$ versus $V_{gs}$ for GaAs MESFET with and without optical illumination.
FIGURE 5. MEASURED GAIN VERSUS $V_{GS}$ WITH AND WITHOUT ILLUMINATION. DISTANCE BETWEEN END OF FIBER AND DEVICE: 1 mm; $\lambda = 0.83 \mu$m; $P_{opt} = 1.7 \text{ mW/cm}^2$. 

(A) DEVICE AlGaAs/GaAs HEMT (MODEL NO. MPD-2503); V$_{ds} = 3.5$ V. 

(B) DEVICE, GaAs MESFET (MODEL NO. DXL-0503 A); V$_{ds} = 3.0$ V.
FIGURE 6. - MEASURED S-PARAMETERS FOR AlGaAs/GaAs HEMT WITH AND WITHOUT ILLUMINATION WHEN BIASED CLOSE TO PINCH-OFF. START 0.045 GHz, STOP 26.5 GHz.
FIGURE 7. - DE-EMBEDDED GATE, SOURCE, AND GATE TO DRAIN CAPACITANCES FROM THE MEASURED S-PARAMETERS WITH AND WITHOUT OPTICAL ILLUMINATION FOR ALGaAS/GaAs HEMT.
S\textsubscript{21} LOG MAG

\begin{align*}
\text{REF.} & \quad 0.0 \text{ dB} \\
V\text{gs (V)} & \\
-5 & \\
-6 & \\
-7 & \\
-8 & \\
-9 & \\
-9.5 & \\
\end{align*}

(A) \text{S}\textsubscript{21} MAGNITUDE WITHOUT OPTICAL ILLUMINATION.

\begin{align*}
\text{REF.} & \quad 0.0^\circ \\
& \\
100.0^\circ / & \\
-9 & \\
-8 & \\
-7 & \\
-6 & \\
-5 & \\
-9.5 & \\
\end{align*}

(B) \text{S}\textsubscript{21} MAGNITUDE WITH OPTICAL ILLUMINATION.

\begin{align*}
\text{START} & \quad 0.045 \text{ GHz} \\
\text{STOP} & \quad 26.500 \text{ GHz} \\
\center & \\
\text{SPAN} & \quad 10.0 \text{ MHz} \\
\text{SPAN} & \quad 10 \text{ MHz} \\
\end{align*}

(C) \text{S}\textsubscript{21} PHASE WITHOUT OPTICAL ILLUMINATION.

(D) \text{S}\textsubscript{21} PHASE WITH OPTICAL ILLUMINATION.

FIGURE 8. - MEASURED \text{S}\textsubscript{21} FOR \text{ALGAA/GAAS HEMT}.

\begin{align*}
\text{CENTER} & \quad 3.000 \text{ GHz} \\
\text{SPAN} & \quad 10.0 \text{ MHz} \\
\text{(A) DETECTED 6 GHz SIGNAL.} & \\
\text{CENTER} & \quad 3.000 \text{ GHz} \\
\text{SPAN} & \quad 10 \text{ MHz} \\
\text{(B) 3 GHz IF SIGNAL.} & \\
\end{align*}

FIGURE 9.
Microwave Performance of an Optically Controlled AlGaAs/GaAs High Electron Mobility Transistor and GaAs MESFET

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Direct current and also the microwave characteristics of optically illuminated AlGaAs/GaAs HEMT are experimentally measured for the first time and compared with that of GaAs MESFET. The results showed that the average increase in the gain is 2.8 dB under 1.7 mW/cm² optical intensity at 0.83 μm. Further, the effect of illumination on S-parameters is more pronounced when the devices are biased close to pinch-off. Novel applications of optically illuminated HEMT as a variable gain amplifier, high-speed high-frequency photo detector, and mixer are demonstrated.

AlGaAs/GaAs HEMT; GaAs MESFET; Optical control; Microwave integrated circuits

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